

HIGH EFFICIENCY GLASS PASSIVATED RECTIFIER

HER501G THRU HER508G

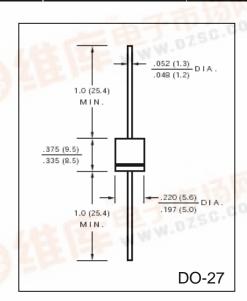
VOLTAGE RANGE CURRENT 50 to 1000 Volts 5.0 Ampere

FEATURES

- Glass passivated chip junction
- Low power loss, high efficiency
- Low Leakage
- High speed switching
- High Surge Capacity
- High Temperature soldering guaranteed: 260 °C / 10 second, 0.375" (9.5mm) lead length

MECHANICAL DATA

- Case: Transfer molded plastic
- Epoxy: UL94V 0 rate flame retardant
- Polarity: Color Band denotes cathode end
- Lead: Plated axial lead, solderable per MIL STD-202E Method 208C
- Mounting Position: Any
- Weight: 0.042 ounce, 1.19 gram



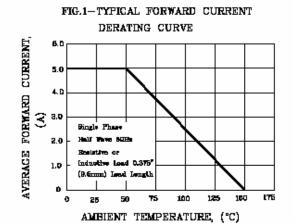
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

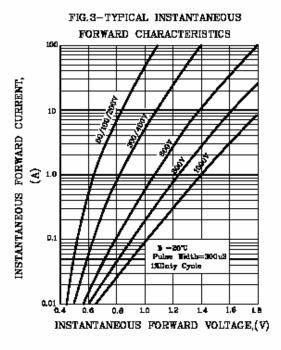
- Ratings at 25°C ambient temperature unless otherwise specified
- Single Phase, half wave, 60Hz, resistive or inductive load
- For capacitive load derate current by 20%

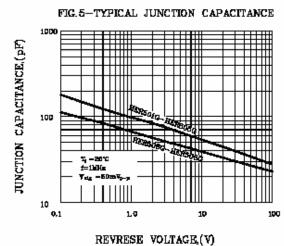
	SYMBOLS	HER 501G	HER 502G	HER 503G	HER 504G	HER 505G	HER 506G	HER 507G	HER 508G	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	Volts
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	Volts
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	Volts
Maximum Average Forward Rectified Current, 0.375 ° (9.5mm) lead length at $T_A = 50$ °C	I _(AV)	5.0								Amps
Peak Forward Surge Current										
8.3mS single half sine wave superimposed on	I_{FSM}	200					150			
rated load (JEDEC method)		100						-TD M		1.0
Maximum Instantaneous Forward Voltage @ 5.0A	$V_{\rm F}$		1.0		1	.3	1.5	7.51	.7	Volts
Maximum DC Reverse Current at Rated $T_A = 25$ °C	,	10								
DC Blocking Voltage per element $T_A = 125$ °C	I_R	500							μΑ	
Maximum Full Load Reverse Current, Full Cycle average 0.375 " (9.5mm) lead length at $T_L = 55$ °C	I _{R(AV)}	150								μΑ
Maximum Reverse Recovery Time Test conditions $I_F = 0.5A$, $I_R = 1.0A$, $I_{RR} = 0.25A$	t_{rr}	50 70						0	nS	
Typical Junction Capacitance (Measured at 1.0MHz and applied reverse voltage of 4.0V)	C_{J}	70 50						0	pF	
Typical Thermal Resistance (Note 1)	$R_{\theta JA}$	20								^o C/W
Operating Junction Temperature	T_{J}	(-55 to +150)								оС
Storage Temperature Rang	T_{STG}	(-55 to +150)								оС

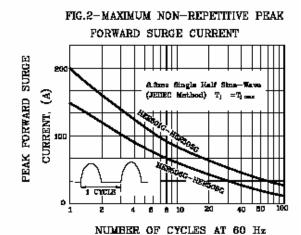


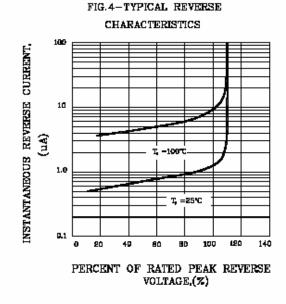
RATINGS AND CHARACTERISTIC CURVES HER501G THRU HER508G

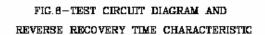


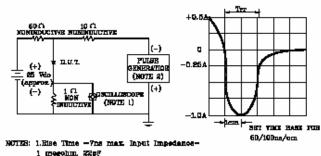












1 megohm. ZZpF 2. Pies time=10ns max. Source impe

80 ohmu